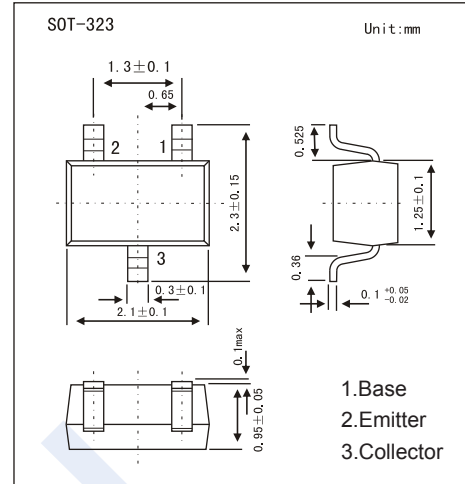


PNP Transistors

MMST2907A (MMST2907A)

■ Features

- Epitaxial planar die construction
- Complementary to MMST2222A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CEO}	-60	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-600	mA
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

PNP Transistors

MMST2907A (MMST2907A)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μ A, I _E = 0	-60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B = 0	-60			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μ A, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-100	nA
Collector-emitter cut-off current	I _{CES}	V _{CB} =-30V, I _B =0			-100	
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-150 mA, I _B =-15mA			-0.4	V
		I _C = -500 mA, I _B = -50mA			-1.6	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-150 mA, I _B =-15mA	-0.6		-1.3	
		I _C = -500 mA, I _B = -50mA			-2.6	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C =- 0.1mA	75			
	h _{FE(2)}	V _{CE} = -10V, I _C = -1mA	100			
	h _{FE(3)}	V _{CE} = -10V, I _C =- 10mA	100			
	h _{FE(4)}	V _{CE} = -10V, I _C = -150mA	100		300	
	h _{FE(5)}	V _{CE} = -10V, I _C = -500mA	50			
Delay time	t _d	V _{CC} =-30V, V _{BE(off)} = 1.5V, I _C =150mA I _{B1} =- 15mA			10	nS
Rise time	t _r				40	
Storage time	t _s	V _{CC} =-30V, I _C =-150mA, I _{B1} =-I _{B2} =-15mA			80	
Fall time	t _f				30	
Emitter input capacitance	C _{ib}	V _{EB} = -2V, I _C = 0, f=1MHz			30	pF
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz			8	
Transition frequency	f _T	V _{CE} = -20V, I _C = -50mA, f=100MHz	200			MHz

■ Marking

Marking	K3F
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